



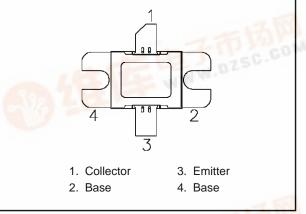
SD1541-01

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

- DESIGNED FOR HIGH POWER PULSED IFF AND DME APPLICATIONS
- 400 (min.) DME 1025 1150 MHz
- 6.5 dB MIN. GAIN
- REFRACTORY GOLD METALLIZATION
- EMITTER BALLASTING AND LOW THERMAL RESISTANCE FOR RELIABILITY AND RUGGEDNESS
- 30:1 LOAD VSWR CAPABILITY AT SPECIFICIED OPERATING CONDITIONS
- INPUT/OUTPUT MATCHED, COMMON BASE CONFIGURATION



PIN CONNECTION



DESCRIPTION

The SD1541-01 is a hermetically sealed, gold metallized, silicon NPN power transistor. The SD1541-01 is designed for applications requiring high peak power and low duty cycles such as DME. The SD1541-01 is packaged in a hermetic metal/ceramic package with internal input/output matching, resulting in improved broadband performance and a low thermal resistance.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Symbol Parameter		Unit	
Vсво	Collector-Base Voltage	65	V	
V _{CES}	Collector-Emitter Voltage	65	V	
V _{EBO} Emitter-Base Voltage		3.5	V	
lc	Device Current	22	A	
PDISS Power Dissipation		1458	W	
TJ	Junction Temperature	+200	°C	
TSTG	Storage Temperature	– 65 to +150	°C	

THERMAL DATA

RTH(j-c)	Junction-Case Thermal Resistance	0.12	°C/W	
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ELECTRICAL SPECIFICATIONS ($T_{case} = 25^{\circ}C$)

STATIC

Symbol	Test Conditions		Value			Unit	
		Test conditions		Min.	Тур.	Max.	Unit
ВУсво	lc = 25mA	$I_E = 0mA$		65	_		V
BVCES	I _C = 50mA	$V_{BE} = 0V$		65	_		V
BV _{EBO}	$I_E = 10 mA$	$I_{C} = 0mA$		3.5	—		V
I _{CES}	$V_{CE} = 50V$	$I_E = 0mA$		—	—	25	mA
hFE	$V_{CE} = 5V$	I _C = .25A		5		200	

DYNAMIC

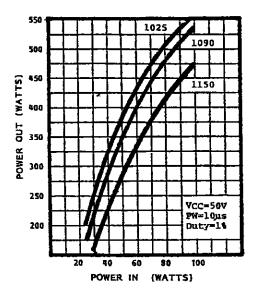
Symbol	Test Conditions		Value		Unit	
Symbol	Symbol Test Conditions			Тур.		Max.
Pout	$f = 1025 - 1150MHz P_{IN} = 90 W V_{CE} = 50$	V	400	_		W
GP	$f = 1025 - 1150MHz P_{IN} = 90 W V_{CE} = 50$	V	6.5	—		dB

Note: Pulse Width = 10μ Sec, Duty Cycle = 1%

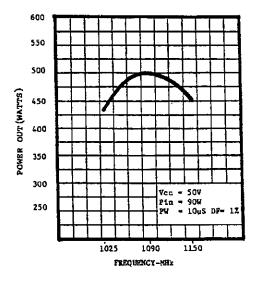
This device is suitable for use under other pulse width/duty cycle conditions. Please contact the factory for specific applications assistance.

TYPICAL PERFORMANCE

POWER OUTPUT vs POWER INPUT



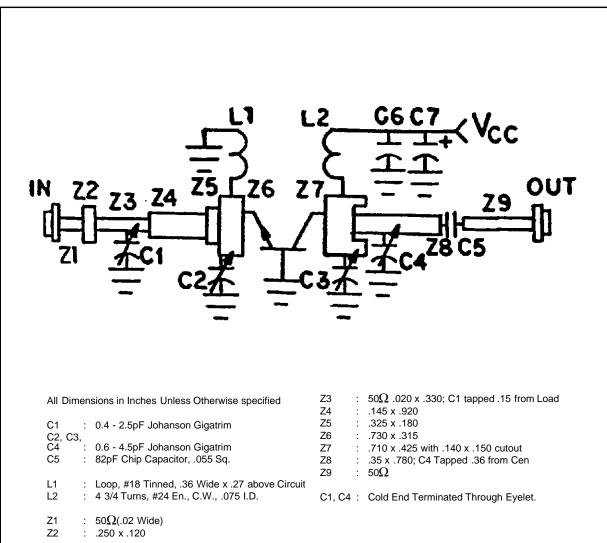
POWER OUTPUT vs FREQUENCY



IMPEDANCE DATA

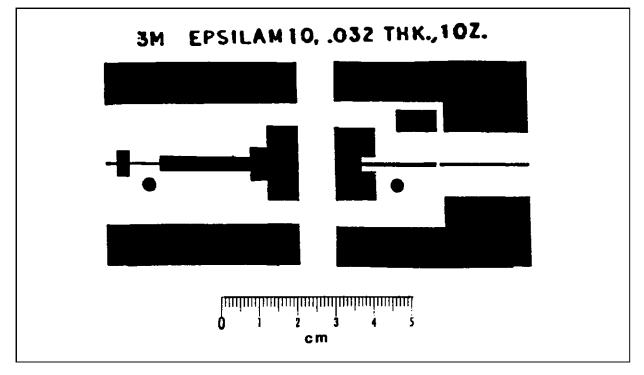
FREQ.	Z _{IN} (Ω)	Z _{CL} (Ω)
1020 MHz	2.898 + j 4.1	1.382 – j 3.2
1090 MHz	2.325 + j 3.4	1.338 – j 2.8
1150 MHz	1.994 + j 2.8	1.269 – j 2.5

TEST CIRCUIT

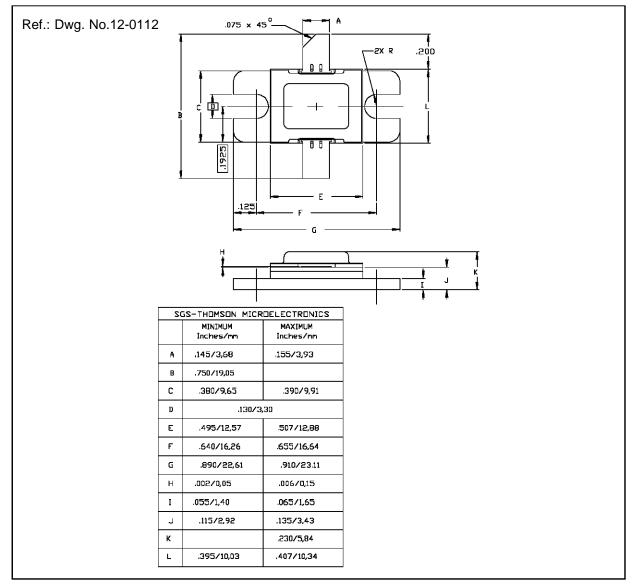


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PC BOARD LAYOUT



PACKAGE MECHANICAL DATA



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